TM20H06DF

N+N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

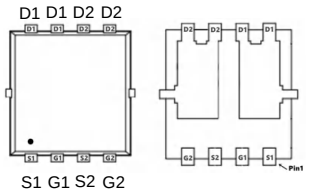
V_{DS} = 60V I_D =20A

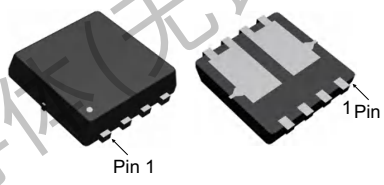
$R_{DS(ON)}$ =25mΩ(Typ.) @ V_{GS}=10V

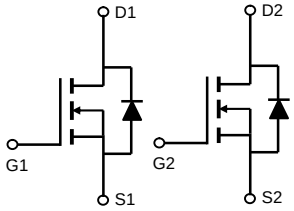
100% UIS Tested

100% R_g Tested

DF:DFN3x3-8L







Marking:20H06

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V	20	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V	15	A
I_{DM}	Pulsed Drain Current	80	A
EAS	Single Pulse Avalanche Energy	30	mJ
P_D@T_C=25℃	Total Power Dissipation	17	W
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	---	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	7.3	℃/W

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Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=60V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	1.0	2.0	3.0	V
$R_{DS(ON)}$	Drain-Source On Resistance	V_{GS}=10V,I_D=10A	---	25	30	mΩ
		V_{GS}=4.5V,I_D=5A	---	34	40	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1MHz	---	983	---	pF
C_{oss}	Output Capacitance		---	68	--	
C_{rss}	Reverse Transfer Capacitance		---	63	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=30V, I_D=20A, R_G=3Ω ,V_{GS}=10V	---	7	---	ns
t_r	Rise Time		---	21	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	16.8	---	ns
t_f	Fall Time		---	24	---	ns
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=30V, I_D=10A	---	26	---	nC
Q_{gs}	Gate-Source Charge		---	4.5	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	6.5	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=20A	---	---	1.2	V
I_S	Continuous Drain Curren	V_D=V_G=0V	---	---	20	A
I_{SM}	Pulsed Drain Current		---	---	80	A
Trr	Reverse Recovery Time	I_F=10A,T_J=25℃ dI/dt=100A/us	---	29	---	ns
Qrr	Reverse Recovery Charge		---	49	---	nC

■ TYPICAL CHARACTERISTICS

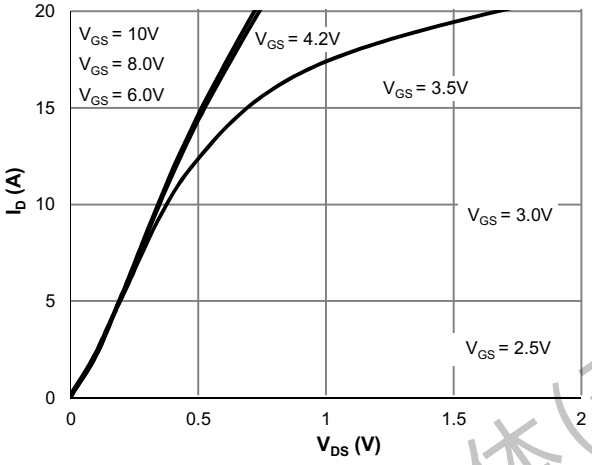


Figure 1: Saturation Characteristics

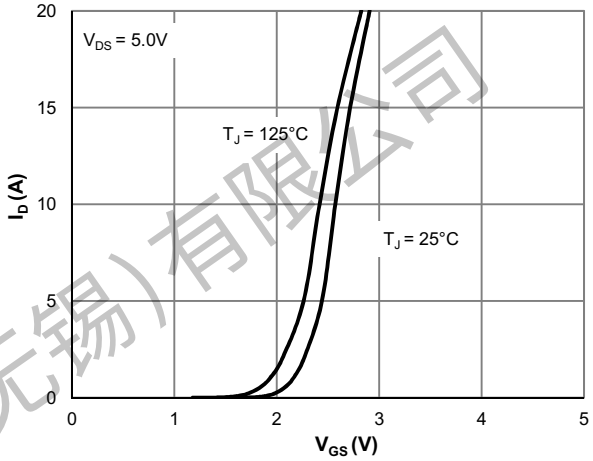


Figure 2: Transfer Characteristics

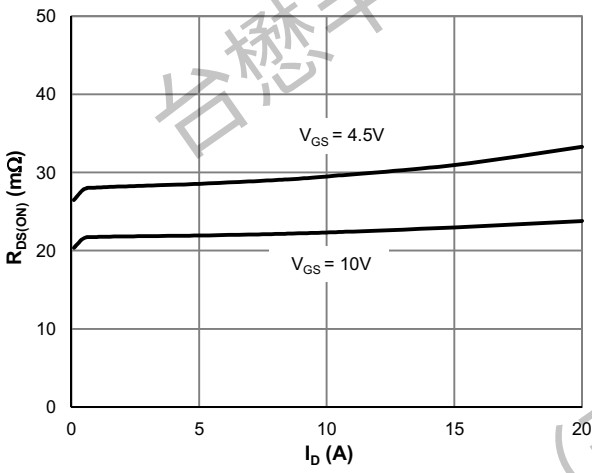


Figure 3: $R_{DS(ON)}$ vs. Drain Current

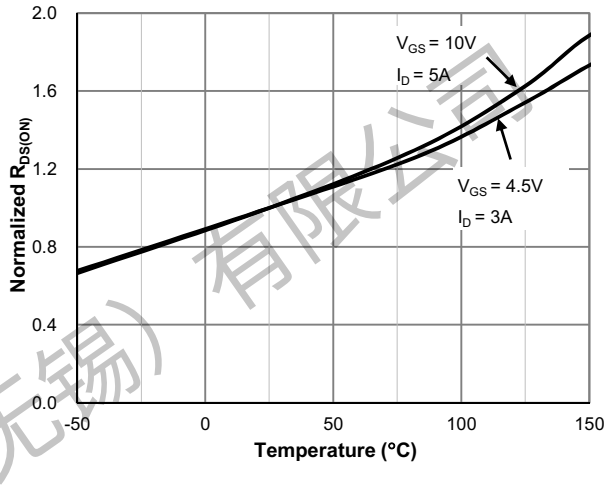


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

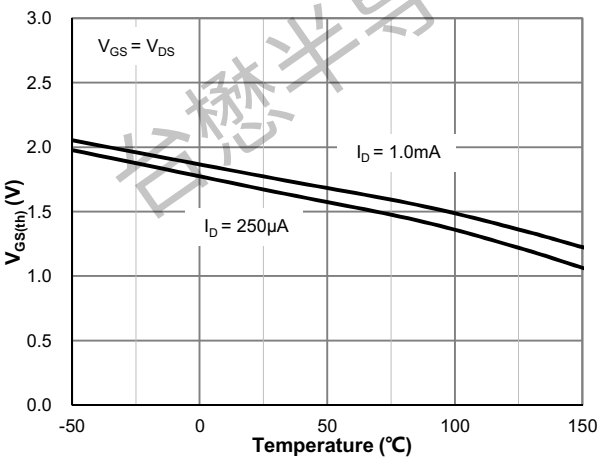


Figure 5: VGS(th) vs. Junction Temperature

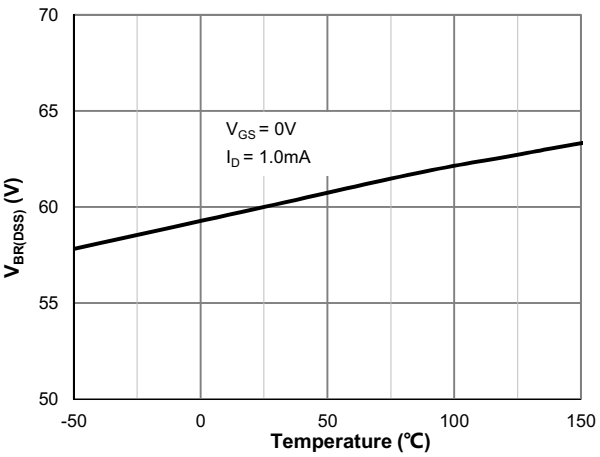


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

■ TYPICAL CHARACTERISTICS(Cont.)

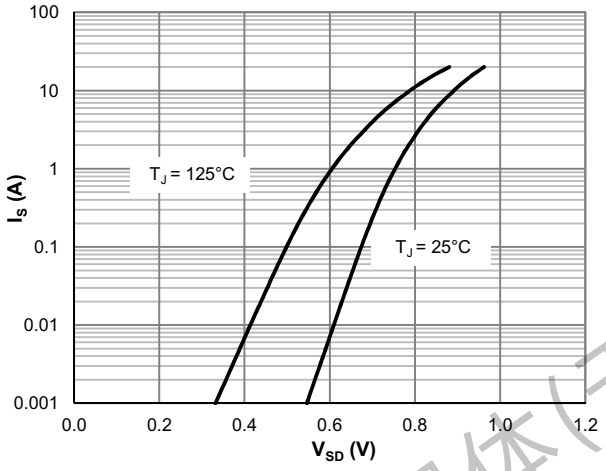


Figure 7: Body-Diode Characteristics

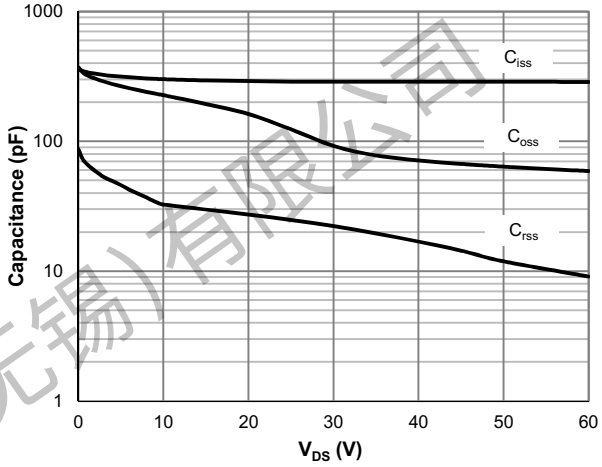


Figure 8: Capacitance Characteristics

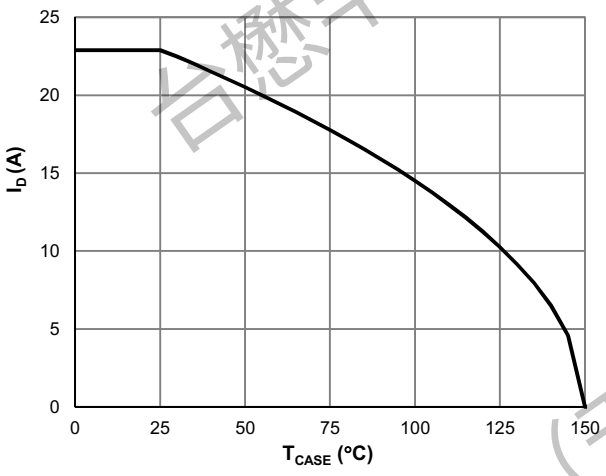


Figure 9: Current De-rating

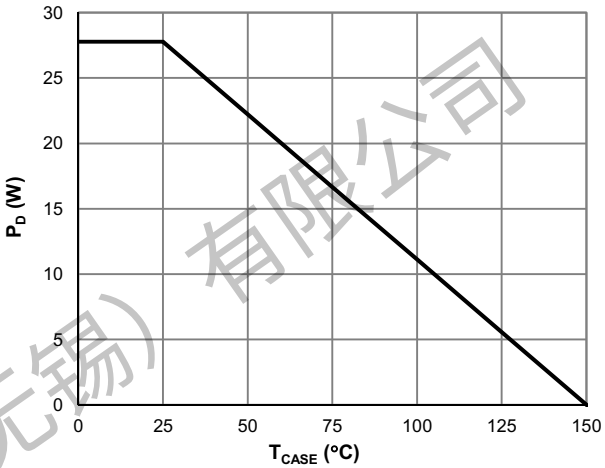


Figure 10: Power De-rating

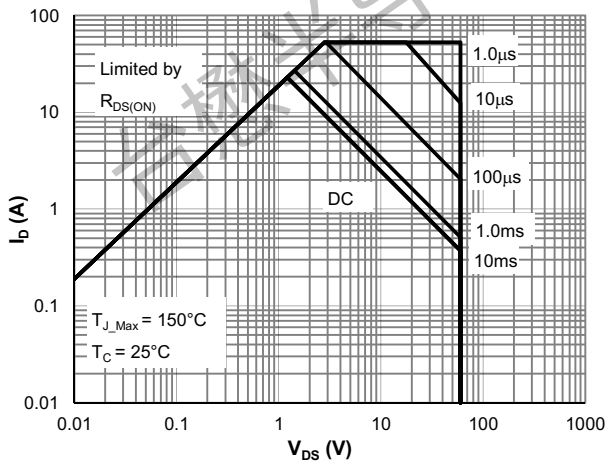


Figure 11: Maximum Safe Operating Area

■ TYPICAL CHARACTERISTICS(Cont.)

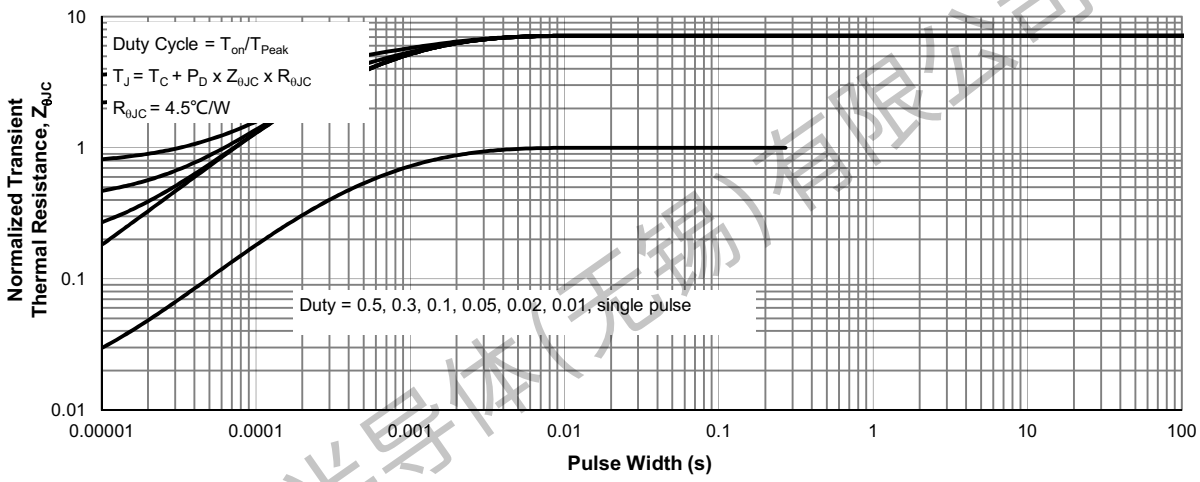
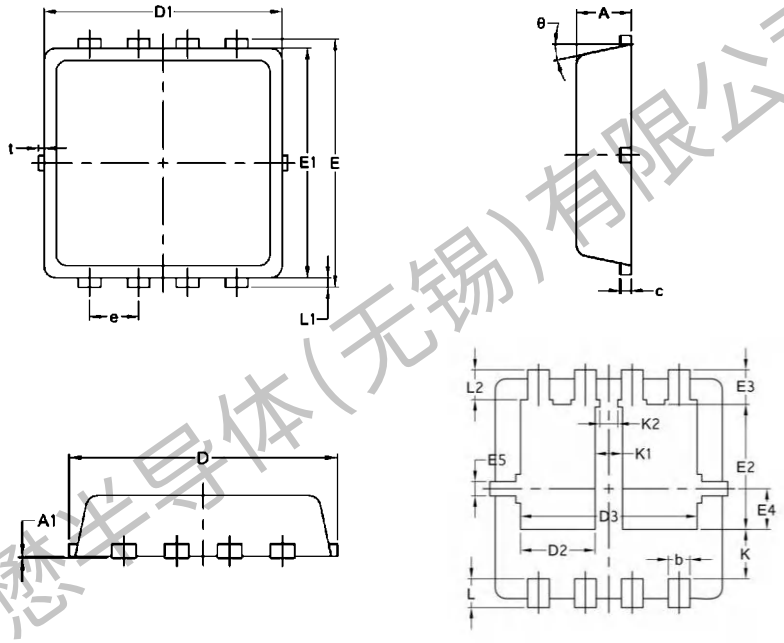


Figure 12: Normalized Maximum Transient Thermal Impedance

Package Mechanical Data:DFN3x3-8L



Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°

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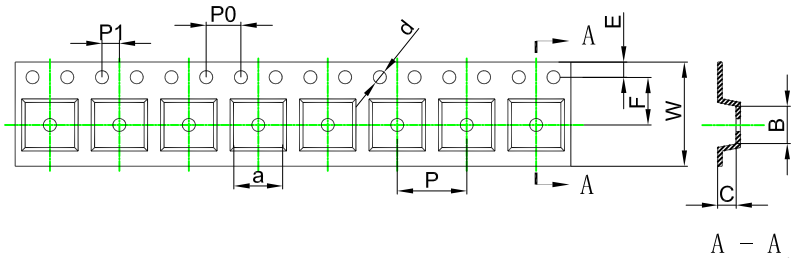
PDFN3×3-8L Embossed Carrier Tape



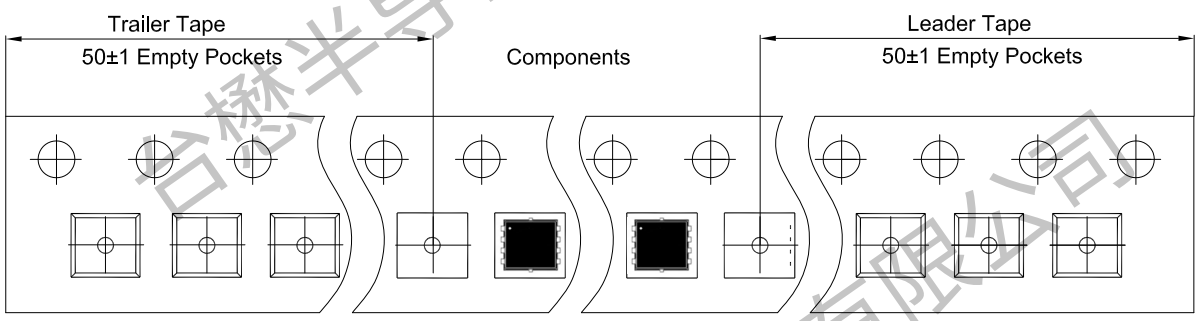
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

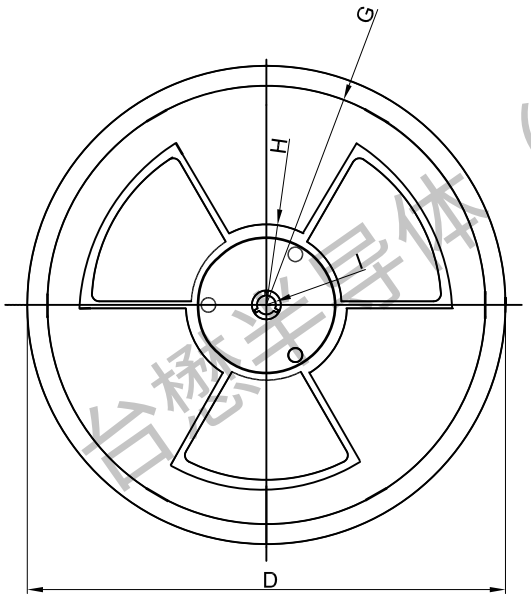
ALL DIM IN mm

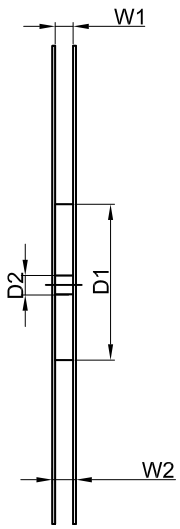
Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN3×3-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN3×3-8L Tape Leader and Trailer



PDFN3×3-8L Reel





Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2023.05.14	23.05	Original	